

What is claimed is:

1. A thin film transistor comprising:  
an insulator substrate;  
a gate electrode located on the insulator substrate;  
a gate insulator film provided above the insulator  
substrate and the gate electrode; and  
a polycrystalline silicon film located on the gate  
insulator film, the polycrystalline silicon film being  
[formed by irradiating a laser beam on a surface of an  
amorphous silicon film to heat the amorphous silicon film],  
the gate electrode having a center portion with a flat  
surface and a pair of tapered end portions with inclined  
surfaces, an angle between each of the inclined surfaces of  
the pair of tapered end portions and a surface of the  
insulator substrate being set within a range of 5° to 40° so  
that [a uniform grain size of the polycrystalline silicon  
film is acquired by securing a gate withstand voltage of the  
thin film transistor and preventing the inclined surfaces of  
the pair of tapered end portions from increasing], wherein  
[the laser beam is scanned on the surface of the amorphous  
silicon film such that laser energy increases in order of  
the substrate, one of the pair of tapered end portions, and  
the center portion].

BEST AVAILABLE COPY